UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 6,941,415 B1

Page 1 of 9

APPLICATION NO.: 09/641519

: September 6, 2005

INVENTOR(S)

: Kevin J. Ryan

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page should be deleted and substitute therefore the attached title page as shown on the attached page.

Drawings:

Delete drawing sheets 1-7, and substitute therefore the drawing sheets, consisting of Figs. 1-7, as shown on the attached pages.

Claim 20, column 9, line 30, "Link" should read --link--.

Signed and Sealed this

Tenth Day of October, 2006

JON W. DUDAS Director of the United States Patent and Trademark Office



(12) United States Patent Ryan

(10) Patent No.:

US 6,941,415 B1

(45) Date of Patent:

Sep. 6, 2005

(54) DRAM WITH H	IDDEN REFRESH
------------------	---------------

- (75) Inventor: Kevin J. Ryan, Eagle, ID (US)
- Assignee: Micron Technology, Inc., Boise, ID (US)

Subject to any disclaimer, the term of this (*) Notice: patent is extended or adjusted under 35 U.S.C. 154(b) by 274 days.

(21)	Appl.	No.:	09/641,519
------	-------	------	------------

(22) Filed:	Aug.	21.	2000
(44	, rucu.	Aug.	41.	2000

- (51) Int. Cl.⁷ G06F 12/00 (52) U.S. Cl. 711/106; 711/167; 711/168
- (58) Field of Search 711/104, 105, 711/100, 167, 168; 305/222, 189.01, 200,

(56)References Cited

U.S. PATENT DOCUMENTS

4,172,282 A	• 10/1979	Aichelmann et al 365/222
4,601,018 A		Baum et al 365/200
4,807,289 A	• 2/1989	Nakajima 704/251
4,849,936 A	• 7/1989	Mizutani 365/189.01
5,638,529 A	* 6/1997	Yee et al 711/106
5,651,131 A	• 7/1997	Chesley 711/106
5,802,555 A	• 9/1998	Shigeeda 365/193
RE36,180 E	4/1999	Lim 365/189.04
5,959,923 A	• 9/1999	Matteson et al 365/222
5 000 474 A	• 17/1999	Leung et al 365/222

2/2000 Leung 365/222 6,028,804 A 6,167,484 A • 12/2000 Boyer et al. 365/222 6,415,353 B1 * 7/2002 Leung 711/106

OTHER PUBLICATIONS

"MoSys Explains 1T-SRAM Technology," by Peter N. Glaskowsky, Microprocessor Report, vol. 13, No. 12, Sep. 13, 1999.

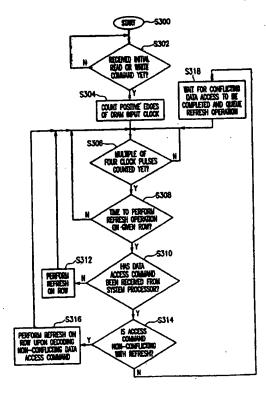
* cited by examiner

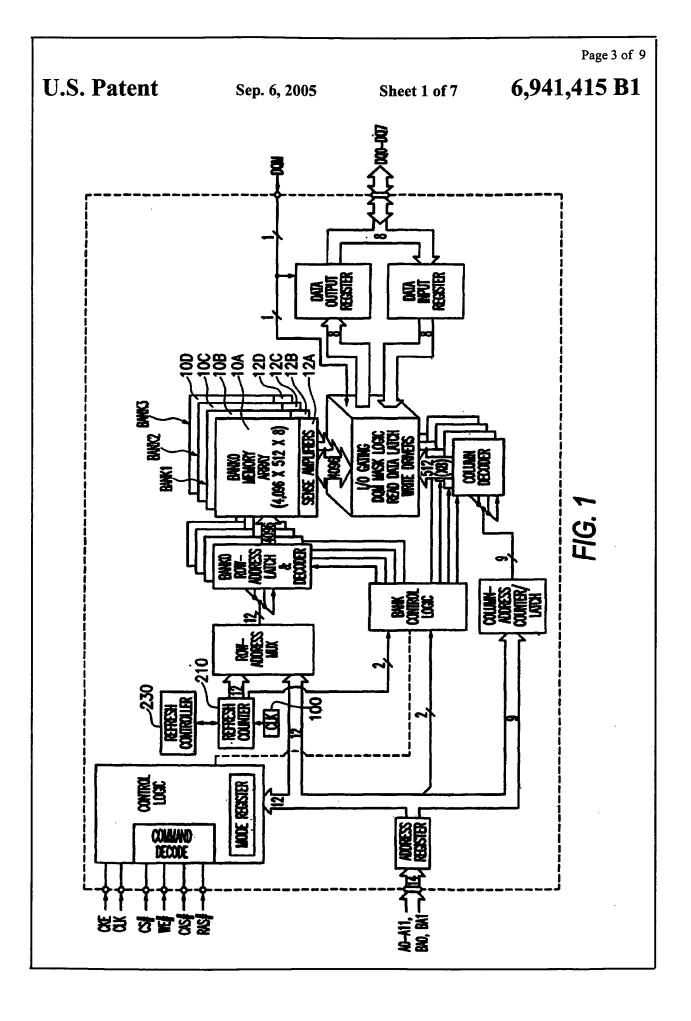
Primary Examiner-Brian R. Peugh (74) Attorney, Agent, or Firm-Dickstein Shapiro Morin & Oshinsky LLP

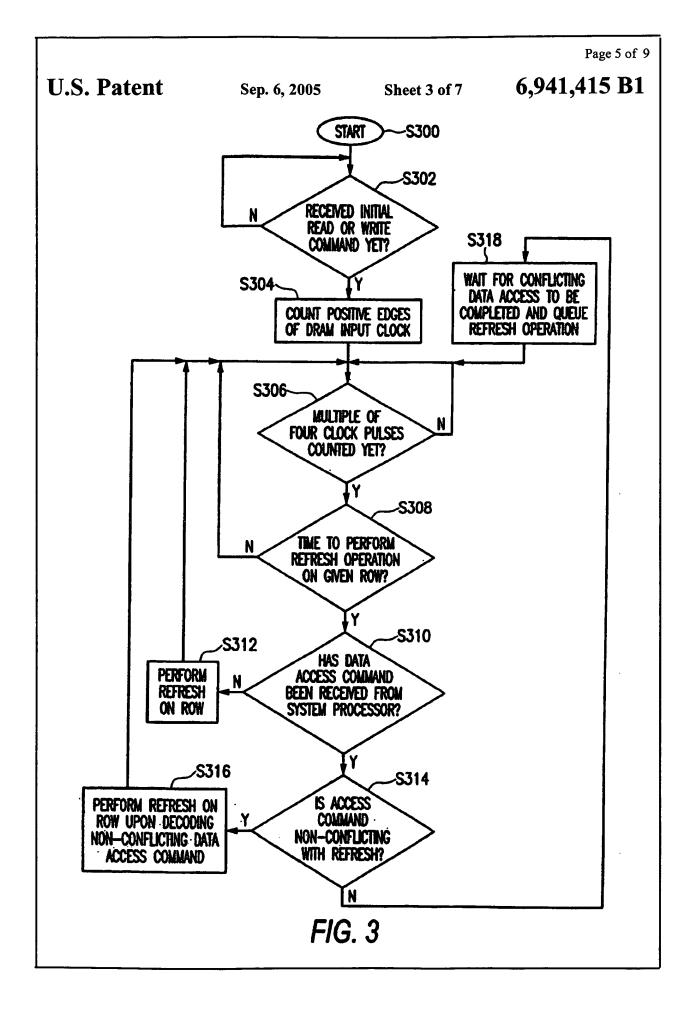
(57)**ABSTRACT**

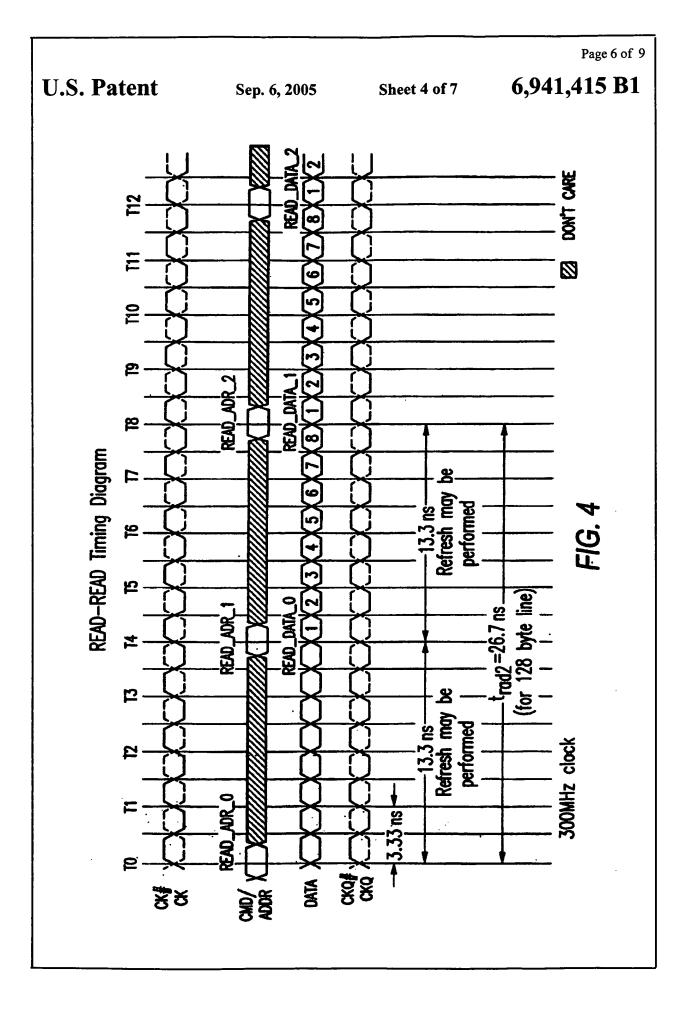
A synchronous DRAM is provided having specified time slots (e.g., every multiple of 4 clock pulses of a DRAM input clock) within which read or write commands may be entered on the command/address bus. During operation, the DRAM performs internally generated refresh operations on a periodic basis while avoiding collisions with controllergenerated data accesses. An internal refresh cycle can be executed without interfering with any data accesses by starting the refresh after decoding a non-conflicting command in one of these time slots and finishing before the next command time slot. If an internal refresh operation is delayed (e.g., by the decoding of a conflicting access command) it will be completed at the earliest opportunity thereafter.

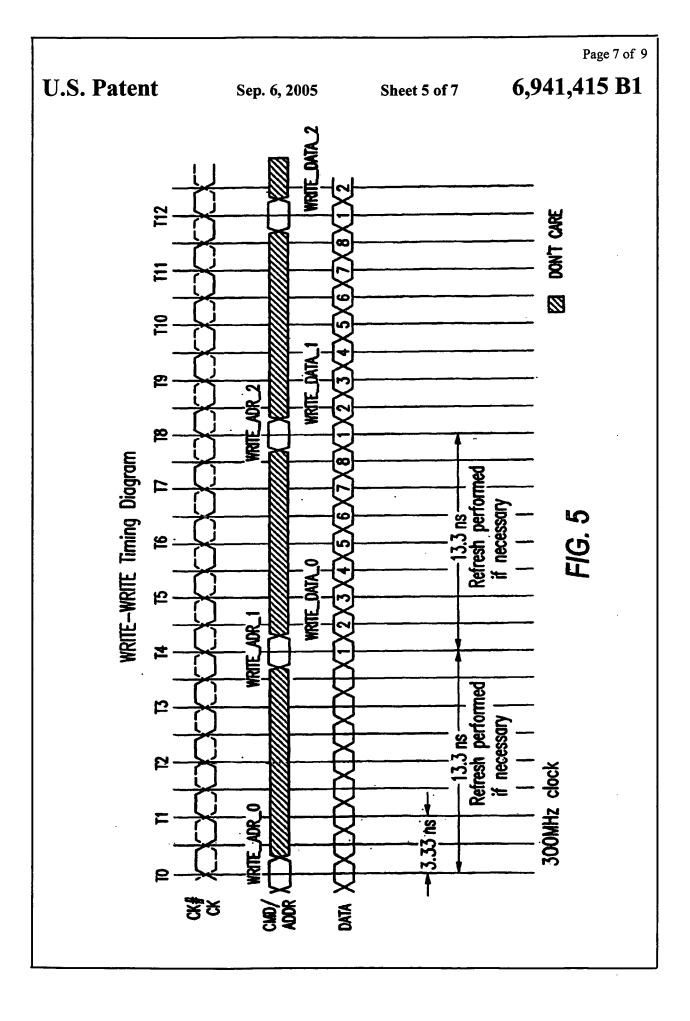
37 Claims, 7 Drawing Sheets











Sep. 6, 2005

Sheet 6 of 7

6,941,415 B1

